

FEATURE

- TrenchFET Power MOSFET

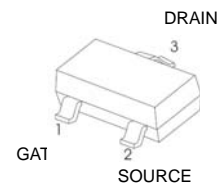
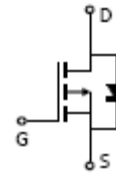
APPLICATIONS

- Load Switch for Portable Devices
- DC/DC Converter

MARKING

- MARKING: 2301

Package



SOT-523

Maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current	I_b	-2.0	A
Pulsed Drain Current	I_{DM}	-6	
Continuous Source-Drain Diode Current	I_s	-0.72	
Maximum Power Dissipation	P_D	0.25	W
Thermal Resistance from Junction to Ambient($t \leq 5s$)	$R_{\theta JA}$	357	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55 ~+150	



Electrical characteristics (Ta=25°C unless otherwise noted)

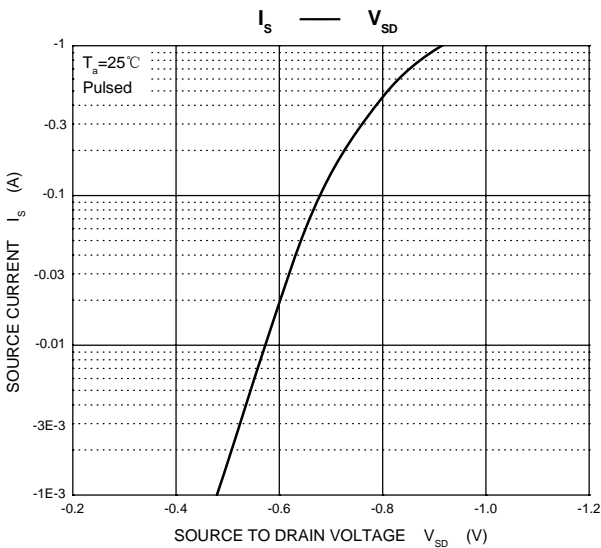
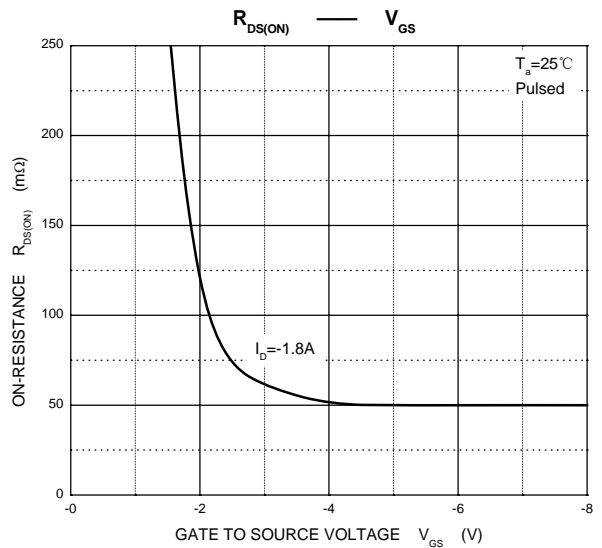
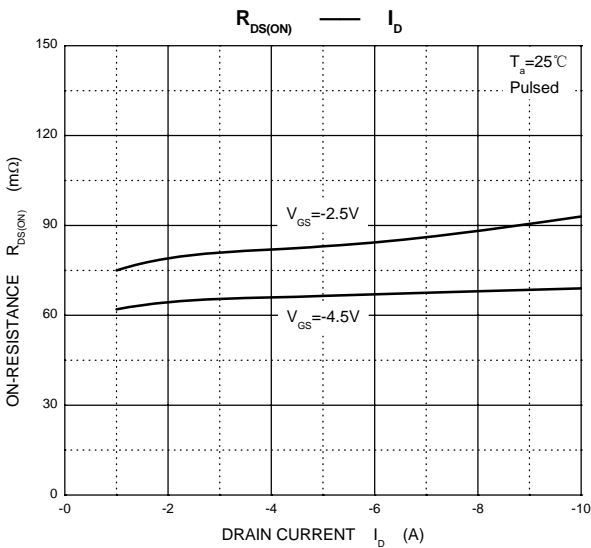
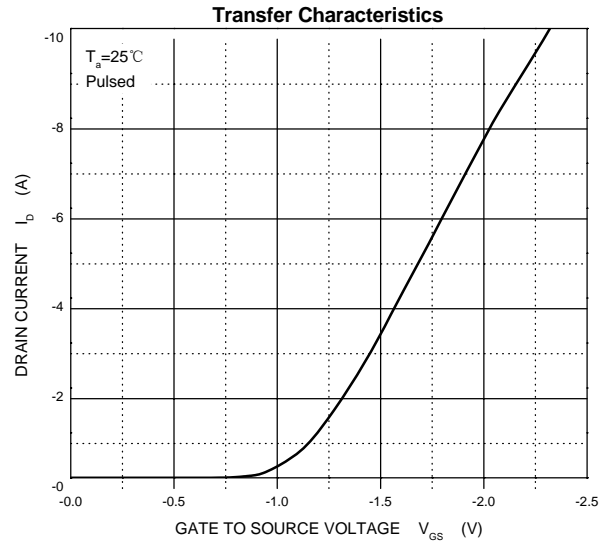
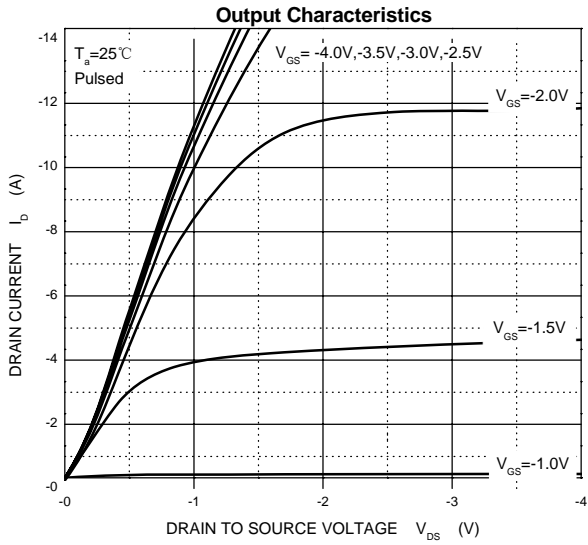
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4		-1	
Gate-source leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -1.8A$		0.125	0.140	Ω
		$V_{GS} = -2.5V, I_D = -1.0A$		0.135	0.180	
Forward trans conductance ^a	g_{fs}	$V_{DS} = -5V, I_D = -2.0A$		6.5		S
Dynamic						
Input capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		405		pF
Output capacitance	C_{oss}			75		
Reverse transfer capacitance	C_{rss}			55		
Total gate charge	Q_g	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -3A$		5.5	10	nC
Gate-source charge	Q_{gs}	$V_{DS} = -10V, V_{GS} = -2.5V, I_D = -3A$		3.3	6	
Gate-drain charge	Q_{gd}				0.7	
Gate resistance	R_g	$f = 1MHz$		6.0		Ω
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -10V, R_L = 10\Omega, I_D = -1A, V_{GEN} = -4.5V, R_g = 1\Omega$		11	20	ns
Rise time	t_r			35	60	
Turn-off delay time	$t_{d(off)}$			30	50	
Fall time	t_f			10	20	
Drain-source body diode characteristics						
Continuous source-drain diode current	I_S	$T_C = 25^\circ C$			-1.3	A
Pulse diode forward current ^a	I_{SM}				-10	
Body diode voltage	V_{SD}	$I_S = -0.7A$		-0.8	-1.2	V

Notes :

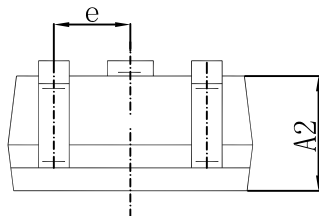
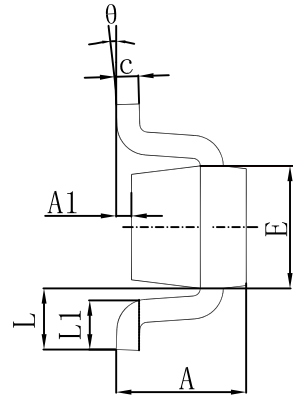
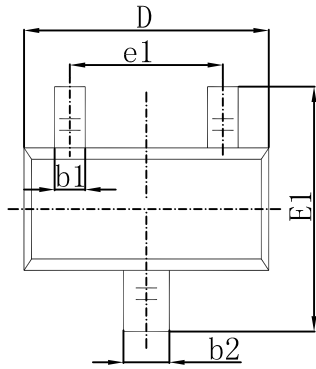
- a.Pulse Test : Pulse Width < 300 μs , Duty Cycle $\leq 2\%$.
- b.Guaranteed by design, not subject to production testing.



Typical Characteristics

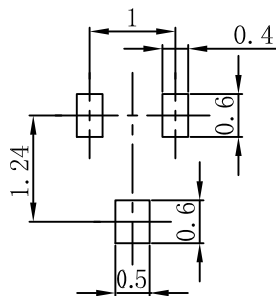


SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

SOT-523 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: ±0.05mm.
 3. The pad layout is for reference purposes only.